NCP1595, NCP1595A, NCP1595C

Buck Regulator-Synchronous

1 MHz, 1.5 A

The NCP1595/A/C family are fixed 1 MHz, high−output−current, synchronous PWM converters that integrate a low−resistance, high−side P−channel MOSFET and a low−side N−channel MOSFET. The NCP1595/A/C utilizes current mode control to provide fast transient response and excellent loop stability. It regulates input voltages from 4.0 V to 5.5 V down to an output voltage as low as 0.8 V and is able to supply up to 1.5 A.

The NCP1595/A/C includes an internally fixed switching frequency (Fsw), and an internal soft−start to limit inrush currents. Using the EN pin, shutdown supply current is reduced to 3 μA maximum.

Other features include cycle−by−cycle current limiting, short−circuit protection and thermal shutdown.

Features

- Input Voltage Range: from 4.0 V to 5.5 V
- Internal 140 mΩ High−Side Switching P−Channel MOSFET and 90 mΩ Low−Side N−Channel MOSFET
- Fixed 1 MHz Switching Frequency
- Cycle−by−Cycle Current Limiting
- Overtemperature Protection
- Internal Soft−Start
- Diode Emulation During Light Load (Disabled for NCP1595C)
- Hiccup Mode Short−Circuit Protection
- Start−up with Pre−Biased Output Load
- Adjustable Output Voltage Down to 0.8 V
- These are Pb−Free Devices

Applications

- DSP Power
- Hard Disk Drivers
- Computer Peripherals
- Home Audio
- Set−Top Boxes
- Networking Equipment
- LCD TV
- Wireless and DSL/Cable Modem
- USB Power Devices

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DFN6
CASE 506AH

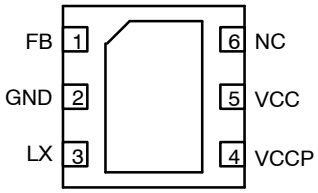
MARKING DIAGRAM



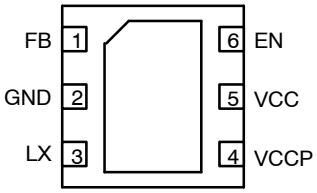
XXXXX = N1595, 1595A, 1595C
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

PIN CONNECTIONS



NCP1595/NCP1595C



NCP1595A

ORDERING INFORMATION

Device	Package	Shipping†
NCP1595MNR2G	DFN6 (Pb−Free)	3000 / Tape & Reel
NCP1595MNT2G		
NCP1595AMNR2G		
NCP1595AMNTWG		
NCP1595CMNTWG		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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BLOCK DIAGRAM

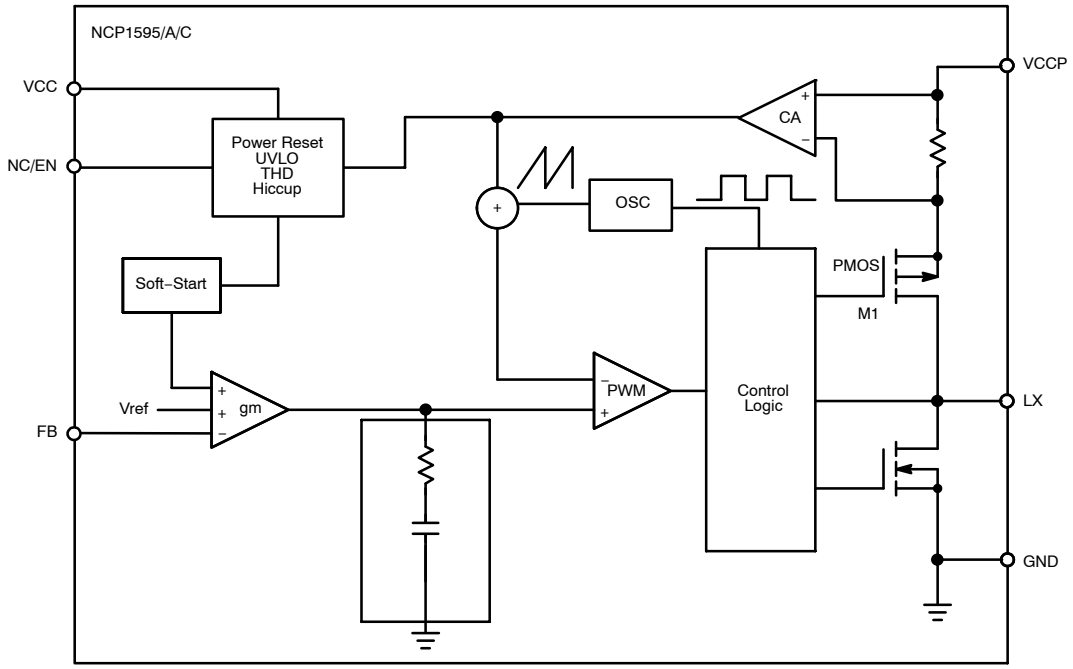


Figure 1. Block Diagram

PIN DESCRIPTIONS

Pin No	Symbol	Description
1	FB	Feedback input pin of the Error Amplifier. Connect a resistor divider from the converter's output voltage to this pin to set the converter's output voltage.
2	GND	Ground pin. Connect to thermal pad.
3	LX	The drains of the internal MOSFETs. The output inductor should be connected to this pin.
4	V_{CCP}	Power input for the power stage
5	V_{CC}	Input supply pin for internal bias circuitry. A 0.1 μF ceramic bypass capacitor is preferred to connect to this pin.
6	NC	No connection for NCP1595 or NCP1595C
	EN	Logic input to enable the part. Logic high to turn on the part and logic low to shut off the part. An internal pullup forces the part into an enable state when no external bias is present on the pin. For NCP1595A only
EP	PAD	Exposed pad of the package provides both electrical contact to the ground and good thermal contact to the PCB. This pad must be soldered to the PCB for proper operation.

APPLICATION CIRCUIT

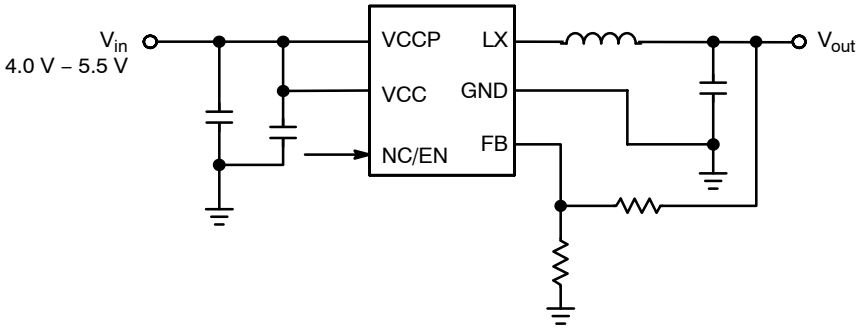


Figure 2. NCP1595/A/C

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Power Supply Pin (Pin 4, 5) to GND	V_{in}	6.5 −0.3 (DC) −1.0 (t < 100 ns)	V
LX to GND	LX	V_{in} + 0.7 V_{in} + 1.0 (t < 20 ns) −0.7 (DC) −5.0 (t < 100 ns)	V
All other pins		6.0 −0.3 (DC) −1.0 (t < 100 ns)	V
Operating Temperature Range	T_A	−40 to +125	°C
Junction Temperature	T_J	−40 to +150	°C
Storage Temperature Range	T_S	−55 to +150	°C
Thermal Resistance Junction−to−Air (Note 1)	$R_{\theta JA}$	68.5	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. $R_{\theta JA}$ measured on approximately 1x1 inch sq. of 1 oz. Copper.

ELECTRICAL CHARACTERISTICS

(V_{in} = 4.0 V – 5.5 V, V_{out} = 1.2 V, T_J = +25°C for typical value; For NCP1595, NCP1595A: –40°C < T_A < 125°C; For NCP1595C: –40°C < T_A < 85°C for min/max values unless noted otherwise)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
V_{in} Input Voltage Range (Note 2)	V_{in}		4.0		5.5	V
V_{CC} UVLO Threshold			3.2	3.5	3.8	V
UVLO Hysteresis				335		mV
V_{CC} Quiescent Current	I_{inVCC}	V_{in} = 5 V,V_{FB} = 1.5 V, (No Switching)		1.7	2.0	mA
V_{CCP} Quiescent Current	I_{inVCCP}	V_{in} = 5 V,V_{FB} = 1.5 V, (No Switching)		25		μA
V_{in} Shutdown Supply Current (Note 3)	I_{QSHDN}	(NCP1595A), EN = 0 V		1.8	3.0	μA
FEEDBACK VOLTAGE						
Reference Voltage	V_{FB}		0.788	0.800	0.812	V
Feedback Input Bias Current (Note 2)	I_{FB}	V_{FB} = 0.8 V		10	100	nA
Feedback Voltage Line Regulation (Note 3)		V_{in} = 4.0 V to 5.5 V		0.06		%/V
PWM						
Maximum Controllable Duty Cycle (regulating)			82	85		%
Minimum Controllable ON Time (Note 3)				50		ns
PULSE–BY–PULSE CURRENT LIMIT						
Pulse–by–Pulse Current Limit (Regulation)	I_{LIM}		2.7	3.9	4.3	A
Pulse–by–Pulse Current Limit (Soft–Start)	I_{LIMSS}		4.0	5.3	6.1	A
OSCILLATOR						
Oscillator Frequency	F_{SW}		0.87	1.0	1.13	MHz
MOSFET						
High Side MOSFET ON Resistance (Note 2)	$R_{DS(on)}$ HS	I_{DS} = 100 mA, V_{GS} = 5 V		140	200	mΩ
High Side MOSFET Leakage (Note 3)		V_{EN} = 0 V, V_{SW} = 0 V			10	μA
Low Side MOSFET ON Resistance (Note 2)	$R_{DS(on)}$ LS	I_{DS} = 100 mA, V_{GS} = 5 V		90	125	mΩ
Low Side MOSFET Leakage (Note 3)		V_{EN} = 0 V, V_{SW} = 5 V			10	μA
ENABLE (NCP1595A)						
EN HI Threshold	ENHI	(NCP1595A)	1.4			V
EN LO Threshold	ENLO	(NCP1595A)			0.4	V
EN Hysteresis		(NCP1595A)		200		mV
EN Pullup Current		(NCP1595A)		1.4	3.0	μA
SOFT–START						
Soft–Start Ramp Time (Note 3)	t_{SS}	F_{SW} = 1 MHz		1.0		ms
Hiccup Timer (Note 3)				2.0		ms
THERMAL SHUTDOWN						
Thermal Shutdown Threshold (Note 3)				185		°C
Thermal Shutdown Hysteresis (Note 3)				40		°C

2. Guaranteed by characterization. Not production tested.
3. Guaranteed by design. Not production tested.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL OPERATING CHARACTERISTICS

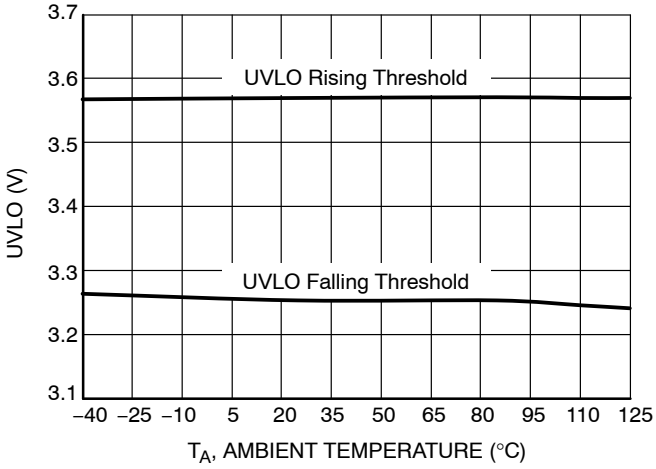


Figure 3. Undervoltage Lockout vs. Temperature

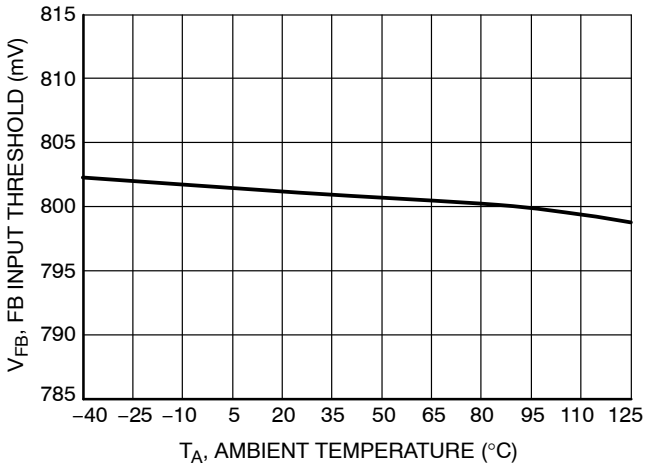


Figure 4. Feedback Input Threshold vs. Temperature

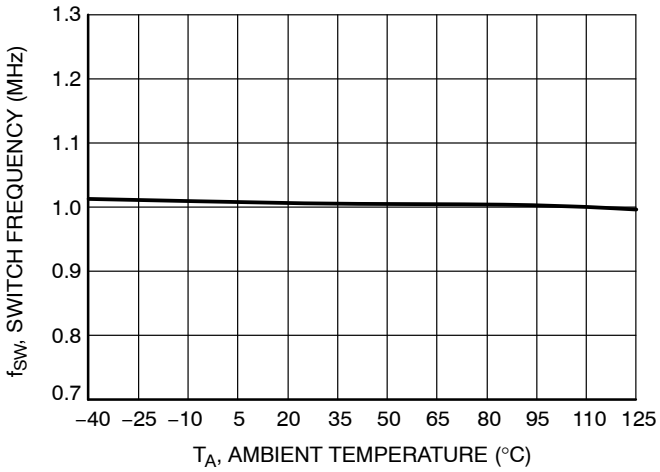


Figure 5. Switching Frequency vs. Temperature

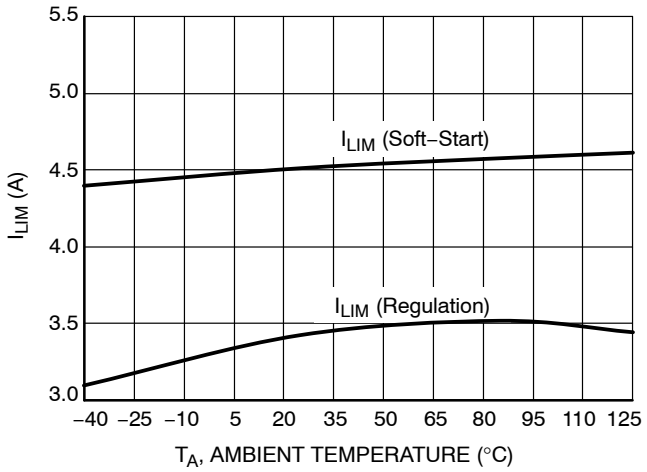


Figure 6. Current Limit vs. Temperature

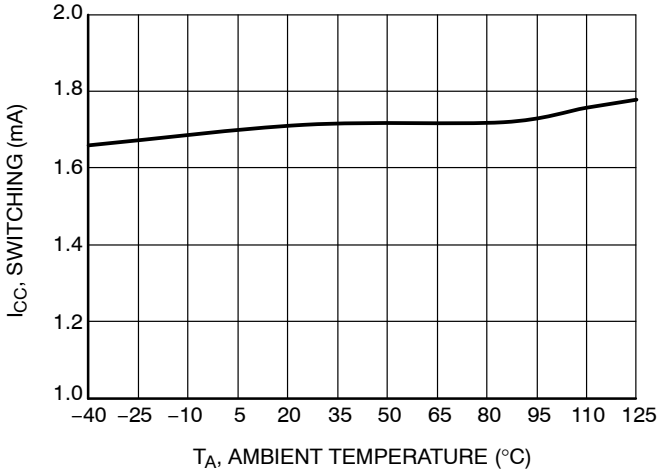


Figure 7. Quiescent Current Into V_{CC} vs. Temperature

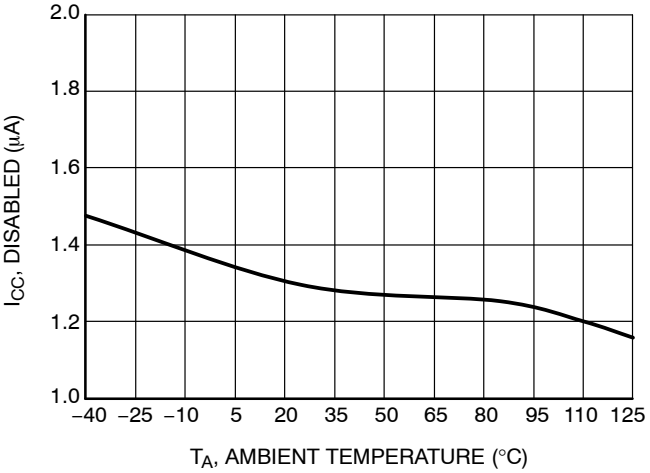


Figure 8. Quiescent Current Into V_{CC} vs. Temperature

TYPICAL OPERATING CHARACTERISTICS

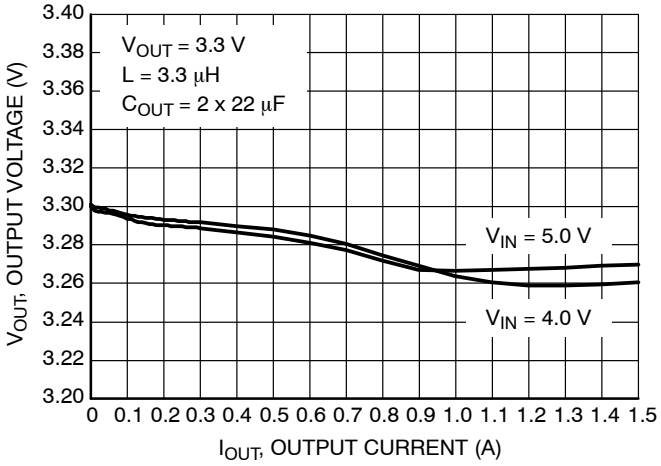


Figure 9. Load Regulation for V_{OUT} = 3.3 V

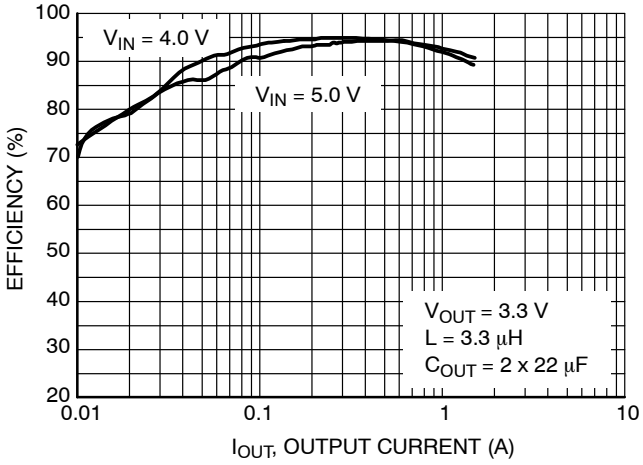


Figure 10. Efficiency vs. Output Current for V_{OUT} = 3.3 V

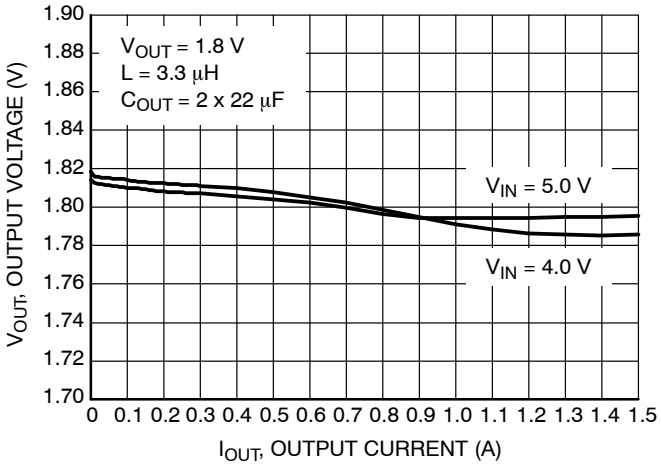


Figure 11. Load Regulation for V_{OUT} = 1.8 V

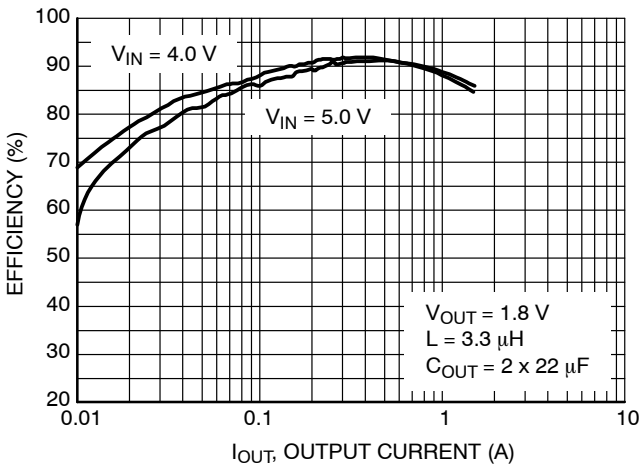


Figure 12. Efficiency vs. Output Current for V_{OUT} = 1.8 V

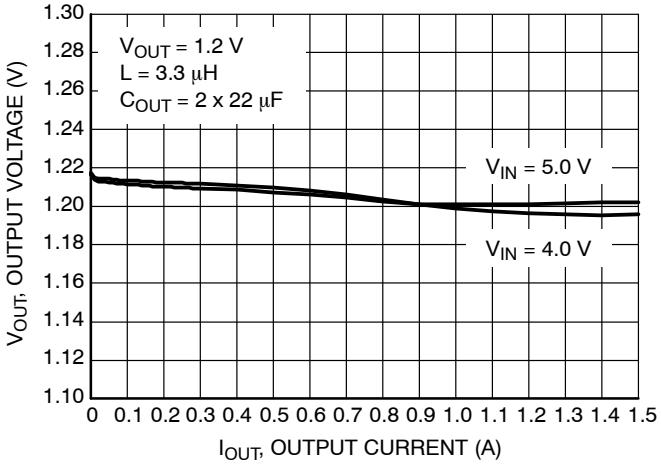


Figure 13. Load Regulation for V_{OUT} = 1.2 V

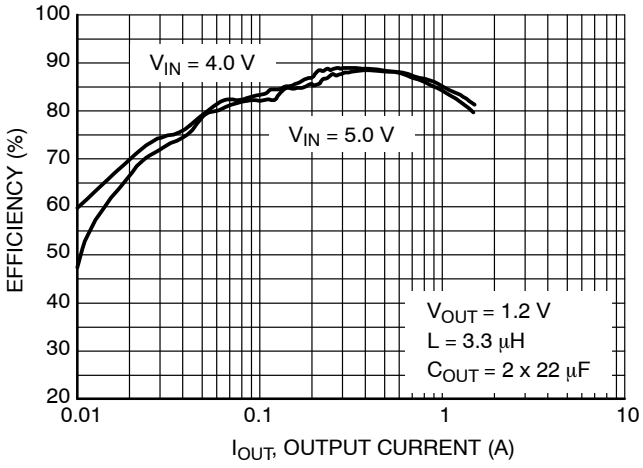
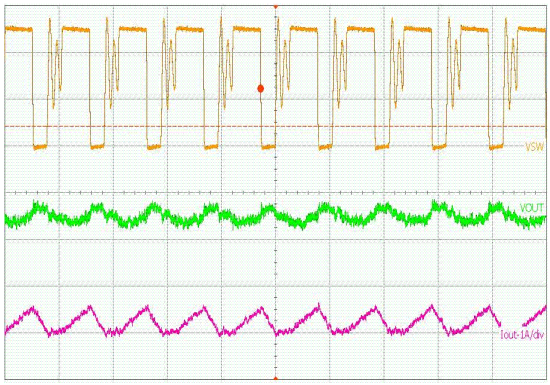
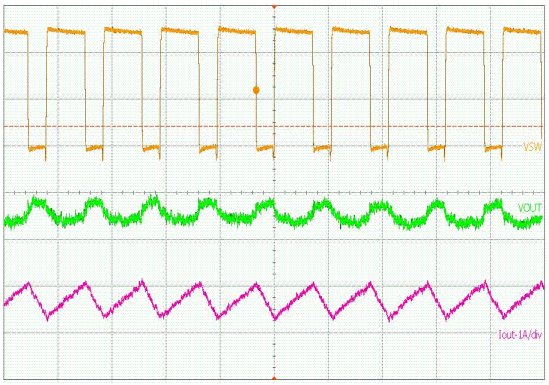


Figure 14. Efficiency vs. Output Current for V_{OUT} = 1.2 V



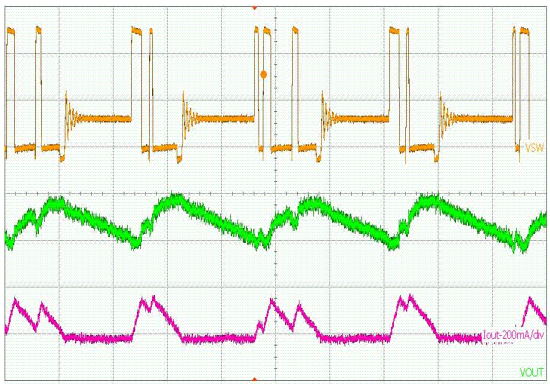
(V_{IN} = 5 V, I_{LOAD} = 100 mA, L = 3.3 μH, C_{OUT} = 2 x 22 μF)
Upper Trace: L_X Pin Switching Waveform, 2 V/div
Middle Trace: Output Ripple Voltage, 20 mV/div
Lower Trace: Inductor Current, 1 A/div
Time Scale: 1.0 μs/div

Figure 15. DCM Switching Waveform for V_{OUT} = 3.3 V



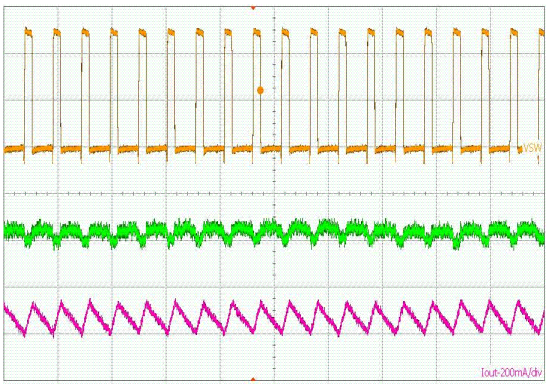
(V_{IN} = 5 V, I_{LOAD} = 700 mA, L = 3.3 μH, C_{OUT} = 2 x 22 μF)
Upper Trace: L_X Pin Switching Waveform, 2 V/div
Middle Trace: Output Ripple Voltage, 20 mV/div
Lower Trace: Inductor Current, 1 A/div
Time Scale: 1.0 μs/div

Figure 16. CCM Switching Waveform for V_{OUT} = 3.3 V



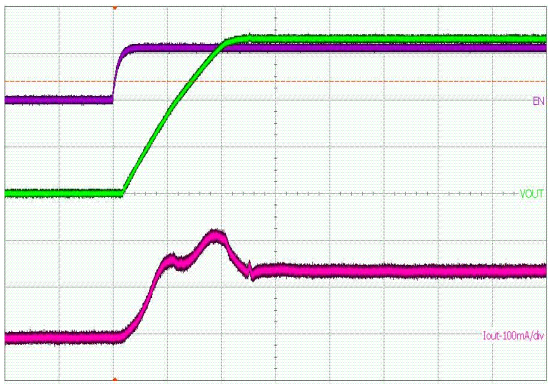
(V_{IN} = 5 V, I_{LOAD} = 100 mA, L = 3.3 μH, C_{OUT} = 2 x 22 μF)
Upper Trace: L_X Pin Switching Waveform, 2 V/div
Middle Trace: Output Ripple Voltage, 20 mV/div
Lower Trace: Inductor Current, 200 mA/div
Time Scale: 1.0 μs/div

Figure 17. DCM Switching Waveform for V_{OUT} = 1.2 V



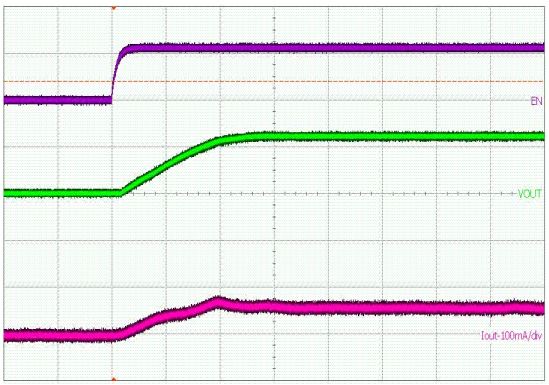
(V_{IN} = 5 V, I_{LOAD} = 400 mA, L = 3.3 μH, C_{OUT} = 2 x 22 μF)
Upper Trace: L_X Pin Switching Waveform, 2 V/div
Middle Trace: Output Ripple Voltage, 20 mV/div
Lower Trace: Inductor Current, 1 A/div
Time Scale: 1.0 μs/div

Figure 18. CCM Switching Waveform for V_{OUT} = 1.2 V



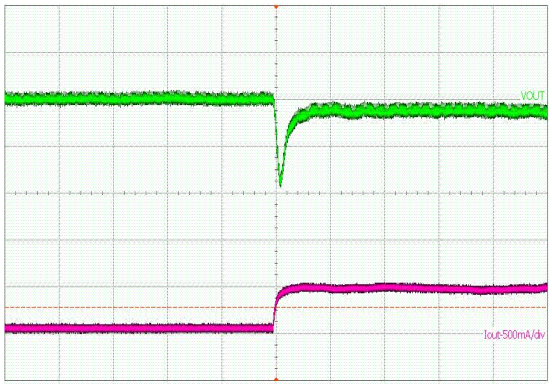
(V_{IN} = 5 V, I_{LOAD} = 100 mA, L = 3.3 μH, C_{OUT} = 2 x 22 μF)
Upper Trace: EN Pin Voltage, 2 V/div
Middle Trace: Output Voltage, 1 V/div
Lower Trace: Inductor Current, 100 mA/div
Time Scale: 500 μs/div

Figure 19. Soft−Start Waveforms for V_{OUT} = 3.3 V



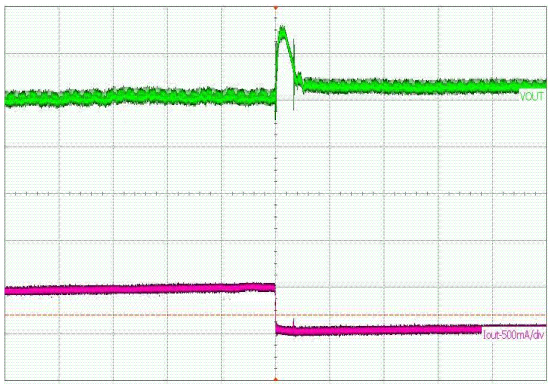
(V_{IN} = 5 V, I_{LOAD} = 100 mA, L = 3.3 μH, C_{OUT} = 2 x 22 μF)
Upper Trace: EN Pin Voltage, 2 V/div
Middle Trace: Output Voltage, 1 V/div
Lower Trace: Inductor Current, 100 mA/div
Time Scale: 500 μs/div

Figure 20. Soft−Start Waveforms for V_{OUT} = 1.2 V



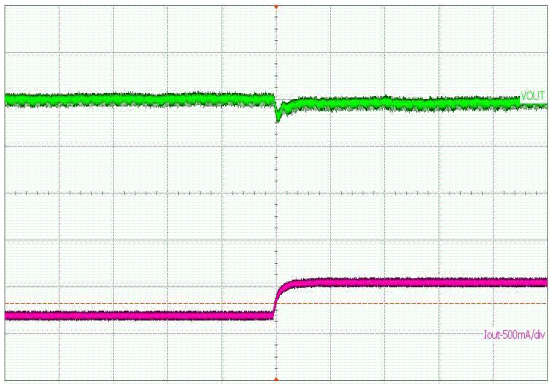
(V_{IN} = 5 V, I_{LOAD} = 100 mA, L = 3.3 μH, C_{OUT} = 2 x 22 μF)
Upper Trace: Output Dynamic Voltage, 100 mV/div
Lower Trace: Output Current, 500 mA/div
Time Scale: 200 μs/div

Figure 21. Transient Response for V_{OUT} = 3.3 V



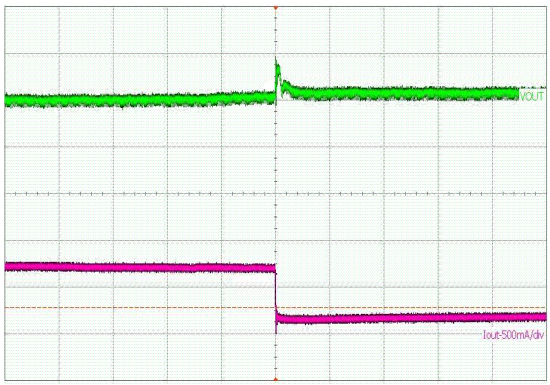
(V_{IN} = 5 V, I_{LOAD} = 100 mA, L = 3.3 μH, C_{OUT} = 2 x 22 μF)
Upper Trace: Output Dynamic Voltage, 100 mV/div
Lower Trace: Output Current, 500 mA/div
Time Scale: 200 μs/div

Figure 22. Transient Response for V_{OUT} = 3.3 V



(V_{IN} = 5 V, I_{LOAD} = 100 mA, L = 3.3 H, C_{OUT} = 2 x 22 μF)
Upper Trace: Output Dynamic Voltage, 100 mV/div
Lower Trace: Output Current, 500 mA/div
Time Scale: 200 μs/div

Figure 23. Transient Response for V_{OUT} = 1.2 V



(V_{IN} = 5 V, I_{LOAD} = 100 mA, L = 3.3 H, C_{OUT} = 2 x 22 μF)
Upper Trace: Output Dynamic Voltage, 100 mV/div
Lower Trace: Output Current, 500 mA/div
Time Scale: 200 μs/div

Figure 24. Transient Response for V_{OUT} = 1.2 V

DETAILED DESCRIPTION

Overview

The NCP1595/A/C is a synchronous PWM controller that incorporates all the control and protection circuitry necessary to satisfy a wide range of applications. The NCP1595/A/C employs current mode control to provide fast transient response, simple compensation, and excellent stability. The features of the NCP1595/A/C include a precision reference, fixed 1 MHz switching frequency, a transconductance error amplifier, an integrated high−side P−channel MOSFET and low−side N−Channel MOSFET, internal soft−start, and very low shutdown current. The protection features of the NCP1595/A/C include internal soft−start, pulse−by−pulse current limit, and thermal shutdown.

Reference Voltage

The NCP1595/A/C incorporates an internal reference that allows output voltages as low as 0.8 V. The tolerance of the internal reference is guaranteed over the entire operating temperature range of the controller. The reference voltage is trimmed using a test configuration that accounts for error amplifier offset and bias currents.

Oscillator Frequency

A fixed precision oscillator is provided. The oscillator frequency range is 1 MHz with $\pm$13% variation.

Transconductance Error Amplifier

The transconductance error amplifier's primary function is to regulate the converter's output voltage using a resistor divider connected from the converter's output to the FB pin of the controller, as shown in the applications Schematic. If a Fault occurs, the amplifier's output is immediately pulled to GND and PWM switching is inhibited.

Internal Soft−Start

To limit the startup inrush current, an internal soft start circuit is used to ramp up the reference voltage from 0 V to its final value linearly. The internal soft start time is 1 ms typically.

Output MOSFETs

The NCP1595/A/C includes low $R_{DS(on)}$, both high−side P−channel and low−side N−channel MOSFETs capable of delivering up to 1.5 A of current. When the controller is disabled or during a Fault condition, the controller's output stage is tri−stated by turning OFF both the upper and lower MOSFETs.

Adaptive Dead Time Gate Driver

In a synchronous buck converter, a certain dead time is required between the low side drive signal and high side drive signal to avoid shoot through. During the dead time, the body diode of the low side FET freewheels the current. The body diode has much higher voltage drop than that of the MOSFET, which reduces the efficiency significantly. The longer the body diode conducts, the lower the efficiency. In NCP1595/A/C, the drivers and MOSFETs are integrated in a single chip. The parasitic inductance is minimized. Adaptive dead time control method is used to prevent the shoot through from happening and minimizing the diode conduction loss at the same time.

Pulse Width Modulation

A high−speed PWM comparator, capable of pulse widths as low as 50 ns, is included in the NCP1595/A/C. The inverting input of the comparator is connected to the output of the error amplifier. The non−inverting input is connected to the the current sense signal. At the beginning of each PWM cycle, the CLK signal sets the PWM flip−flop and the upper MOSFET is turned ON. When the current sense signal rises above the error amplifier's voltage then the comparator will reset the PWM flip−flop and the upper MOSFET will be turned OFF.

Current Sense

The NCP1595/A/C monitors the current in the upper MOSFET. The current signal is required by the PWM comparator and the pulse−by−pulse current limiter.

PROTECTIONS

Undervoltage Lockout (UVLO)

The under voltage lockout feature prevents the controller from switching when the input voltage is too low to power the internal power supplies and reference. Hysteresis must be incorporated in the UVLO comparator to prevent IxR drops in the wiring or PCB traces from causing ON/OFF cycling of the controller during heavy loading at power up or power down.

Overcurrent Protection (OCP)

NCP1595/A/C detects high side switch current and then compares to a voltage level representing the overcurrent threshold limit. If the current through the high side FET exceeds the overcurrent threshold limit for seven consecutive switching cycles, overcurrent protection is triggered.

Once the overcurrent protection occurs, hiccup mode engages. First, hiccup mode, turns off both FETs and discharges the internal compensation network at the output of the OTA. Next, the IC waits typically 2 ms and then resets the overcurrent counter. After this reset, the circuit attempts another normal soft−start. During soft−start, the overcurrent protection threshold is increased to prevent false overcurrent detection while charging the output capacitors. Hiccup mode reduces input supply current and power dissipation during a short circuit. It also allows for much improved system up−time, allowing auto−restart upon removal of a temporary short−circuit.

Power Save Mode

If the load current decreases, the converter can skip switching and operate with reduced frequency. This minimizes the quiescent current and maintains high efficiency. NCP1595C disables this feature.

Pre−Bias Startup

In some applications the controller will be required to start switching when it's output capacitors are charged anywhere from slightly above 0 V to just below the regulation voltage. This situation occurs for a number of reasons: the converter's output capacitors may have residual charge on them or the converter's output may be held up by a low current standby power supply. NCP1595/A/C supports pre−bias start up by holding switching off until the soft−start ramp reaches the FB Pin voltage.

Thermal Shutdown

The NCP1595/A/C protects itself from over heating with an internal thermal monitoring circuit. If the junction temperature exceeds the thermal shutdown threshold both the upper and lower MOSFETs will be shut OFF.

APPLICATION INFORMATION

Programming the Output Voltage

The output voltage is set using a resistive voltage divider from the output voltage to FB pin (see Figure 25). So the output voltage is calculated according to Eq.1.

$$V_{out} = V_{FB} \cdot \frac{R_1 + R_2}{R_2} \quad \text{(eq. 1)}$$

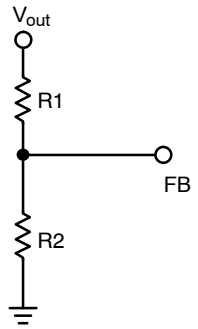


Figure 25. Output divider

Inductor Selection

The inductor is the key component in the switching regulator. The selection of inductor involves trade−offs among size, cost and efficiency. The inductor value is selected according to the equation 2.

$$L = \frac{V_{out}}{f \cdot I_{ripple}} \cdot \left(1 - \frac{V_{out}}{V_{in(max)}}\right) \quad \text{(eq. 2)}$$

Where V_{out} − the output voltage;
f − switching frequency, 1.0 MHz;
I_{ripple} − Ripple current, usually it's 20% − 30% of output current;
$V_{in(max)}$ − maximum input voltage.

Choose a standard value close to the calculated value to maintain a maximum ripple current within 30% of the maximum load current. If the ripple current exceeds this 30% limit, the next larger value should be selected.

The inductor's RMS current rating must be greater than the maximum load current and its saturation current should be about 30% higher. For robust operation in fault conditions (start−up or short circuit), the saturation current should be high enough. To keep the efficiency high, the series resistance (DCR) should be less than 0.1 Ω, and the core material should be intended for high frequency applications.

Output Capacitor Selection

The output capacitor acts to smooth the dc output voltage and also provides energy storage. So the major parameter necessary to define the output capacitor is the maximum allowed output voltage ripple of the converter. This ripple is related to capacitance and the ESR. The minimum capacitance required for a certain output ripple can be calculated by Equation 4.

$$C_{OUT(min)} = \frac{I_{ripple}}{8 \cdot f \cdot V_{ripple}} \quad \text{(eq. 3)}$$

Where V_{ripple} is the allowed output voltage ripple.

The required ESR for this amount of ripple can be calculated by equation 5.

$$ESR = \frac{V_{ripple}}{I_{ripple}} \quad \text{(eq. 4)}$$

Based on Equation 2 to choose capacitor and check its ESR according to Equation 3. If ESR exceeds the value from Eq.4, multiple capacitors should be used in parallel.

Ceramic capacitor can be used in most of the applications. In addition, both surface mount tantalum and through−hole aluminum electrolytic capacitors can be used as well.

Maximum Output Capacitor

NCP1595/A/C family has internal 1 ms fixed soft−start and overcurrent limit. It limits the maximum allowed output capacitor to startup successfully. The maximum allowed output capacitor can be determined by the equation:

$$C_{out(max)} = \frac{I_{lim(min)} - I_{load(max)} - \frac{\Delta i_{p-p}}{2}}{V_{out}/T_{SS(min)}} \quad \text{(eq. 5)}$$

Where $T_{SS(min)}$ is the minimum soft−start period (1ms); D_{iPP} is the current ripple.

This is assuming that a constant load is connected. For example, with 3.3 V/2.0 A output and 20% ripple, the max allowed output capacitors is 546 μF.

Input Capacitor Selection

The input capacitor can be calculated by Equation 6.

$$C_{in(min)} = I_{out(max)} \cdot D_{max} \cdot \frac{1}{f \cdot V_{in(ripple)}} \quad \text{(eq. 6)}$$

Where $V_{in(ripple)}$ is the required input ripple voltage.

$$D_{max} = \frac{V_{out}}{V_{in(min)}} \text{ is the maximum duty cycle.} \quad \text{(eq. 7)}$$

Power Dissipation

The NCP1595/A/C is available in a thermally enhanced 6−pin, DFN. When the die temperature reaches +185°C, the NCP1595/A/C shuts down (see the *Thermal−Overload Protection* section). The power dissipated in the device is the sum of the power dissipated from supply current (PQ), power dissipated due to switching the internal power MOSFET (P_{SW}), and the power dissipated due to the RMS current through the internal power MOSFET (PON). The total power dissipated in the package must be limited so the junction temperature does not exceed its absolute maximum rating of +150°C at maximum ambient temperature.

Calculate the power lost in the NCP1595/A/C using the following equations:

1. High side MOSFET

The conduction loss in the top switch is:

$$P_{HSON} = I^2_{RMS_HSFET} \times R_{DS(on)HS} \quad \text{(eq. 8)}$$

Where:

$$I_{RMS_FET} = \sqrt{\left(I_{out}^2 + \frac{\Delta I_{PP}^2}{12}\right) \times D} \quad \text{(eq. 9)}$$

ΔI_{PP} is the peak−to−peak inductor current ripple.

The power lost due to switching the internal power high side MOSFET is:

$$P_{HSSW} = \frac{V_{in} \cdot I_{out} \cdot \left(t_r + t_f\right) \cdot f_{SW}}{2} \quad \text{(eq. 10)}$$

t_r and t_f are the rise and fall times of the internal power MOSFET measured at SW node.

2. Low side MOSFET

The power dissipated in the top switch is:

$$P_{LSON} = I_{RMS_LSFET}^2 \cdot R_{DS(on)LS} \quad \text{(eq. 11)}$$

Where:

$$I_{RMS_LSFET} = \sqrt{\left(I_{out}^2 + \frac{\Delta I_{PP}^2}{12}\right) \cdot (1 - D)} \quad \text{(eq. 12)}$$

ΔI_{PP} is the peak−to−peak inductor current ripple.

The switching loss for the low side MOSFET can be ignored.

The power lost due to the quiescent current (I_Q) of the device is:

$$P_Q = V_{in} \cdot I_Q \quad \text{(eq. 13)}$$

I_Q is the switching quiescent current of the NCP1595/A/C.

$$P_{TOTAL} = P_{HSON} + P_{HSSW} + P_{LSON} + P_Q \quad \text{(eq. 14)}$$

Calculate the temperature rise of the die using the following equation:

$$T_J = T_C + \left(P_{TOTAL} \cdot \theta_{JC}\right) \quad \text{(eq. 15)}$$

θ_{JC} is the junction−to−case thermal resistance equal to 1.7°C/W. T_C is the temperature of the case and TJ is the junction temperature, or die temperature. The case−to−ambient thermal resistance is dependent on how well heat can be transferred from the PC board to the air. Solder the underside−exposed pad to a large copper GND plane. If the die temperature reaches +185°C the NCP1595/A/C shut down and does not restart again until the die temperature cools by 40°C.

Layout Consideration

As with all high frequency switchers, when considering layout, care must be taken in order to achieve optimal electrical, thermal and noise performance. For 1.0MHz switching frequency, switch rise and fall times are typically in few nanosecond range. To prevent noise both radiated and conducted the high speed switching current path must be kept as short as possible. Shortening the current path will also reduce the parasitic trace inductance of approximately 25 nH/inch. At switch off, this parasitic inductance produces a flyback spike across the NCP1595/A/C switch. When operating at higher currents and input voltages, with poor layout, this spike can generate voltages across the NCP1595/A/C that may exceed its absolute maximum rating. A ground plane should always be used under the switcher circuitry to prevent interplane coupling and overall noise.

The FB component should be kept as far away as possible from the switch node. The ground for these components should be separated from the switch current path. Failure to do so will result in poor stability or subharmonic like oscillation.

Board layout also has a significant effect on thermal resistance. Reducing the thermal resistance from ground pin and exposed pad onto the board will reduce die temperature and increase the power capability of the NCP1595/A/C. This is achieved by providing as much copper area as possible around the exposed pad. Adding multiple thermal vias under and around this pad to an internal ground plane will also help. Similar treatment to the inductor pads will reduce any additional heating effects.

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

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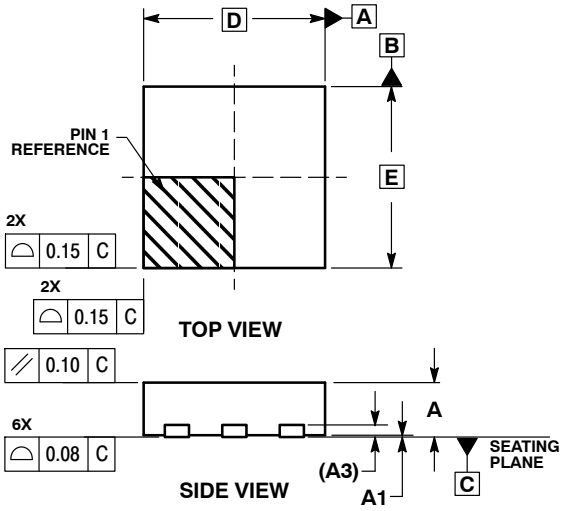


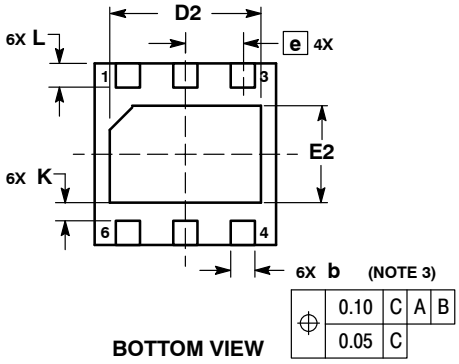
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SCALE 2:1

DFN6 3*3 MM, 0.95 PITCH
CASE 506AH−01
ISSUE O

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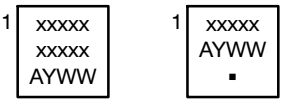




NOTES:
1. DIMENSIONS AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMESNION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.80	0.90	1.00
A1	0.00	0.03	0.05
A3		0.20 REF	
b	0.35	0.40	0.45
D		3.00 BSC	
D2	2.40	2.50	2.60
E		3.00 BSC	
E2	1.50	1.60	1.70
e		0.95 BSC	
K	0.21	---	---
L	0.30	0.40	0.50

GENERIC MARKING DIAGRAM*

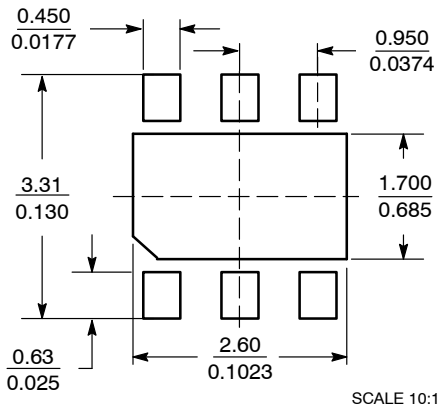


Standard **Pb−Free**

xxxxx	= Specific Device Code
A	= Assembly Location
Y	= Year
WW	= Work Week
▪	= Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking.
Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

SOLDERING FOOTPRINT*



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*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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